

# 1N4728A Series

## 1 Watt DO-41 Hermetically Sealed Glass Zener Voltage Regulator Diodes

This is a complete series of 1 Watt Zener diode with limits and excellent operating characteristics that reflect the superior capabilities of silicon-oxide passivated junctions. All this in an axial-lead hermetically sealed glass package that offers protection in all common environmental conditions.

### Specification Features:

- Zener Voltage Range – 3.3 V to 91 V
- ESD Rating of Class 3 (>16 KV) per Human Body Model
- DO-41 (DO-204AL) Package
- Double Slug Type Construction
- Metallurgical Bonded Construction
- Oxide Passivated Die

### Mechanical Characteristics:

**CASE:** Double slug type, hermetically sealed glass

**FINISH:** All external surfaces are corrosion resistant and leads are readily solderable

### MAXIMUM LEAD TEMPERATURE FOR SOLDERING PURPOSES:

230°C, 1/16" from the case for 10 seconds

**POLARITY:** Cathode indicated by polarity band

**MOUNTING POSITION:** Any

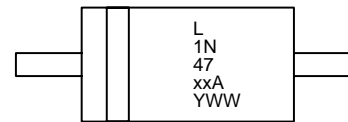
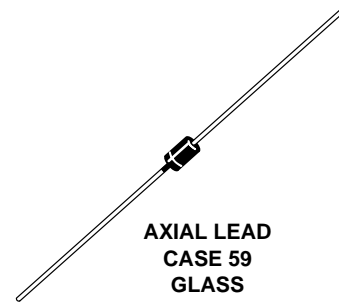
### MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Max. Steady State Power Dissipation @ $T_L \leq 50^\circ\text{C}$ , Lead Length = 3/8" Derated above 50°C	$P_D$	1.0 6.67	Watt mW/°C
Operating and Storage Temperature Range	$T_J, T_{stg}$	- 65 to +200	°C

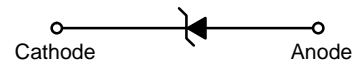


ON Semiconductor™

<http://onsemi.com>



L = Assembly Location  
1N47xxA = Device Code  
Y = Year  
WW = Work Week



### ORDERING INFORMATION (1.)(NO TAG)

Device	Package	Shipping
1N47xxA	Axial Lead	2000 Units/Box
1N47xxARL	Axial Lead	6000/Tape & Reel
1N47xxARL2	Axial Lead	6000/Tape & Reel
1N47xxATA	Axial Lead	4000/Ammo Pack
1N47xxATA2	Axial Lead	4000/Ammo Pack

### NOTES:

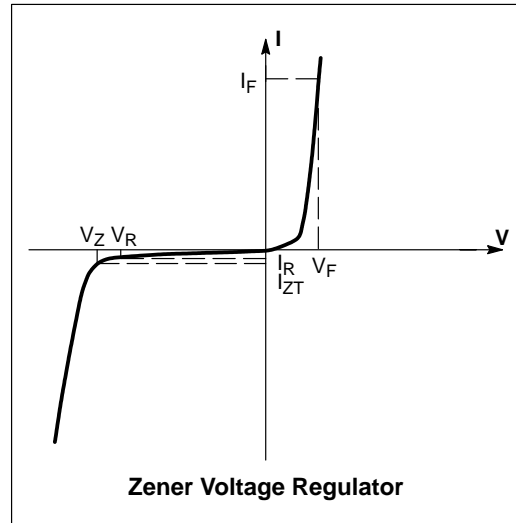
1. The "2" suffix refers to 26 mm tape spacing.

Devices listed in **bold, italic** are ON Semiconductor **Preferred** devices. **Preferred** devices are recommended choices for future use and best overall value.

# 1N4728A Series

**ELECTRICAL CHARACTERISTICS** ( $T_A = 25^\circ\text{C}$  unless otherwise noted,  $V_F = 1.2\text{ V Max.}$ ,  $I_F = 200\text{ mA}$  for all types)

Symbol	Parameter
$V_Z$	Reverse Zener Voltage @ $I_{ZT}$
$I_{ZT}$	Reverse Current
$Z_{ZT}$	Maximum Zener Impedance @ $I_{ZT}$
$I_{ZK}$	Reverse Current
$Z_{ZK}$	Maximum Zener Impedance @ $I_{ZK}$
$I_R$	Reverse Leakage Current @ $V_R$
$V_R$	Breakdown Voltage
$I_F$	Forward Current
$V_F$	Forward Voltage @ $I_F$
$I_r$	Surge Current @ $T_A = 25^\circ\text{C}$



**ELECTRICAL CHARACTERISTICS** ( $T_A = 25^\circ\text{C}$  unless otherwise noted,  $V_F = 1.2\text{ V Max.}$ ,  $I_F = 200\text{ mA}$  for all types)

JEDEC Device (2.)	Zener Voltage (3.)(4.)			Zener Impedance (5.)				Leakage Current		$I_r$ (6.) (mA)
	$V_Z$ (Volts)			@ $I_{ZT}$	$Z_{ZT}$ @ $I_{ZT}$	$Z_{ZK}$ @ $I_{ZK}$		$I_R$ @ $V_R$		
	Min	Nom	Max	(mA)	( $\Omega$ )	( $\Omega$ )	(mA)	( $\mu\text{A Max}$ )	(Volts)	
1N4728A	3.14	3.3	3.47	76	10	400	1	100	1	1380
1N4729A	3.42	3.6	3.78	69	10	400	1	100	1	1260
1N4730A	3.71	3.9	4.10	64	9	400	1	50	1	1190
1N4731A	4.09	4.3	4.52	58	9	400	1	10	1	1070
1N4732A	4.47	4.7	4.94	53	8	500	1	10	1	970
<b>1N4733A</b>	<b>4.85</b>	<b>5.1</b>	<b>5.36</b>	<b>49</b>	<b>7</b>	<b>550</b>	<b>1</b>	<b>10</b>	<b>1</b>	<b>890</b>
<b>1N4734A</b>	<b>5.32</b>	<b>5.6</b>	<b>5.88</b>	<b>45</b>	<b>5</b>	<b>600</b>	<b>1</b>	<b>10</b>	<b>2</b>	<b>810</b>
<b>1N4735A</b>	<b>5.89</b>	<b>6.2</b>	<b>6.51</b>	<b>41</b>	<b>2</b>	<b>700</b>	<b>1</b>	<b>10</b>	<b>3</b>	<b>730</b>
<b>1N4736A</b>	<b>6.46</b>	<b>6.8</b>	<b>7.14</b>	<b>37</b>	<b>3.5</b>	<b>700</b>	<b>1</b>	<b>10</b>	<b>4</b>	<b>660</b>
1N4737A	7.13	7.5	7.88	34	4	700	0.5	10	5	605
<b>1N4738A</b>	<b>7.79</b>	<b>8.2</b>	<b>8.61</b>	<b>31</b>	<b>4.5</b>	<b>700</b>	<b>0.5</b>	<b>10</b>	<b>6</b>	<b>550</b>
1N4739A	8.65	9.1	9.56	28	5	700	0.5	10	7	500
<b>1N4740A</b>	<b>9.50</b>	<b>10</b>	<b>10.50</b>	<b>25</b>	<b>7</b>	<b>700</b>	<b>0.25</b>	<b>10</b>	<b>7.6</b>	<b>454</b>
<b>1N4741A</b>	<b>10.45</b>	<b>11</b>	<b>11.55</b>	<b>23</b>	<b>8</b>	<b>700</b>	<b>0.25</b>	<b>5</b>	<b>8.4</b>	<b>414</b>
<b>1N4742A</b>	<b>11.40</b>	<b>12</b>	<b>12.60</b>	<b>21</b>	<b>9</b>	<b>700</b>	<b>0.25</b>	<b>5</b>	<b>9.1</b>	<b>380</b>
1N4743A	12.4	13	13.7	19	10	700	0.25	5	9.9	344
<b>1N4744A</b>	<b>14.3</b>	<b>15</b>	<b>15.8</b>	<b>17</b>	<b>14</b>	<b>700</b>	<b>0.25</b>	<b>5</b>	<b>11.4</b>	<b>304</b>
<b>1N4745A</b>	<b>15.2</b>	<b>16</b>	<b>16.8</b>	<b>15.5</b>	<b>16</b>	<b>700</b>	<b>0.25</b>	<b>5</b>	<b>12.2</b>	<b>285</b>

### TOLERANCE AND TYPE NUMBER DESIGNATION

2. The JEDEC type numbers listed have a standard tolerance on the nominal zener voltage of  $\pm 5\%$ .

### SPECIALS AVAILABLE INCLUDE:

3. Nominal zener voltages between the voltages shown and tighter voltage tolerances. For detailed information on price, availability, and delivery, contact your nearest ON Semiconductor representative.

### ZENER VOLTAGE ( $V_Z$ ) MEASUREMENT

4. ON Semiconductor guarantees the zener voltage when measured at 90 seconds while maintaining the lead temperature ( $T_L$ ) at  $30^\circ\text{C} \pm 1^\circ\text{C}$ ,  $3/8''$  from the diode body.

### ZENER IMPEDANCE ( $Z_Z$ ) DERIVATION

5. The zener impedance is derived from the 60 cycle ac voltage, which results when an ac current having an rms value equal to 10% of the dc zener current ( $I_{ZT}$  or  $I_{ZK}$ ) is superimposed on  $I_{ZT}$  or  $I_{ZK}$ .

### SURGE CURRENT ( $I_R$ ) NON-REPETITIVE

6. The rating listed in the electrical characteristics table is maximum peak, non-repetitive, reverse surge current of 1/2 square wave or equivalent sine wave pulse of 1/120 second duration superimposed on the test current,  $I_{ZT}$ , per JEDEC registration; however, actual device capability is as described in Figure 5 of the General Data – DO-41 Glass.

# 1N4728A Series

**ELECTRICAL CHARACTERISTICS** ( $T_A = 25^\circ\text{C}$  unless otherwise noted,  $V_F = 1.2\text{ V Max}$ ,  $I_F = 200\text{ mA}$  for all types) (continued)

JEDEC Device (7.)	Zener Voltage (8.)(9.)			Zener Impedance (10.)			Leakage Current		$I_r$ (11.) (mA)	
	$V_Z$ (Volts)			@ $I_{ZT}$	$Z_{ZT}$ @ $I_{ZT}$	$Z_{ZK}$ @ $I_{ZK}$	$I_R$ @ $V_R$			
	Min	Nom	Max	(mA)	( $\Omega$ )	( $\Omega$ )	(mA)	( $\mu\text{A Max}$ )		(Volts)
1N4746A	17.1	18	18.9	14	20	750	0.25	5	13.7	250
1N4747A	19.0	20	21.0	12.5	22	750	0.25	5	15.2	225
1N4748A	20.9	22	23.1	11.5	23	750	0.25	5	16.7	205
1N4749A	22.8	24	25.2	10.5	25	750	0.25	5	18.2	190
1N4750A	25.7	27	28.4	9.5	35	750	0.25	5	20.6	170
1N4751A	28.5	30	31.5	8.5	40	1000	0.25	5	22.8	150
1N4752A	31.4	33	34.7	7.5	45	1000	0.25	5	25.1	135
1N4753A	34.2	36	37.8	7	50	1000	0.25	5	27.4	125
1N4754A	37.1	39	41.0	6.5	60	1000	0.25	5	29.7	115
1N4755A	40.9	43	45.2	6	70	1500	0.25	5	32.7	110
1N4756A	44.7	47	49.4	5.5	80	1500	0.25	5	35.8	95
1N4757A	48.5	51	53.6	5	95	1500	0.25	5	38.8	90
1N4758A	53.2	56	58.8	4.5	110	2000	0.25	5	42.6	80
1N4759A	58.9	62	65.1	4	125	2000	0.25	5	47.1	70
1N4760A	64.6	68	71.4	3.7	150	2000	0.25	5	51.7	65
1N4761A	71.3	75	78.8	3.3	175	2000	0.25	5	56	60
1N4762A	77.9	82	86.1	3	200	3000	0.25	5	62.2	55
1N4763A	86.5	91	95.6	2.8	250	3000	0.25	5	69.2	50

## TOLERANCE AND TYPE NUMBER DESIGNATION

7. The JEDEC type numbers listed have a standard tolerance on the nominal zener voltage of  $\pm 5\%$ .

## SPECIALS AVAILABLE INCLUDE:

8. Nominal zener voltages between the voltages shown and tighter voltage tolerances. For detailed information on price, availability, and delivery, contact your nearest ON Semiconductor representative.

## ZENER VOLTAGE ( $V_Z$ ) MEASUREMENT

9. ON Semiconductor guarantees the zener voltage when measured at 90 seconds while maintaining the lead temperature ( $T_L$ ) at  $30^\circ\text{C} \pm 1^\circ\text{C}$ ,  $3/8"$  from the diode body.

## ZENER IMPEDANCE ( $Z_Z$ ) DERIVATION

10. The zener impedance is derived from the 60 cycle ac voltage, which results when an ac current having an rms value equal to 10% of the dc zener current ( $I_{ZT}$  or  $I_{ZK}$ ) is superimposed on  $I_{ZT}$  or  $I_{ZK}$ .

## SURGE CURRENT ( $I_R$ ) NON-REPETITIVE

11. The rating listed in the electrical characteristics table is maximum peak, non-repetitive, reverse surge current of 1/2 square wave or equivalent sine wave pulse of 1/120 second duration superimposed on the test current,  $I_{ZT}$ , per JEDEC registration; however, actual device capability is as described in Figure 5 of the General Data – DO-41 Glass.

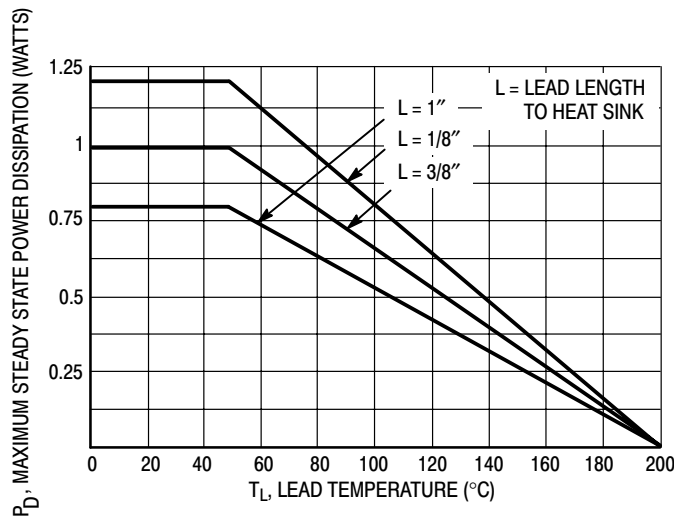
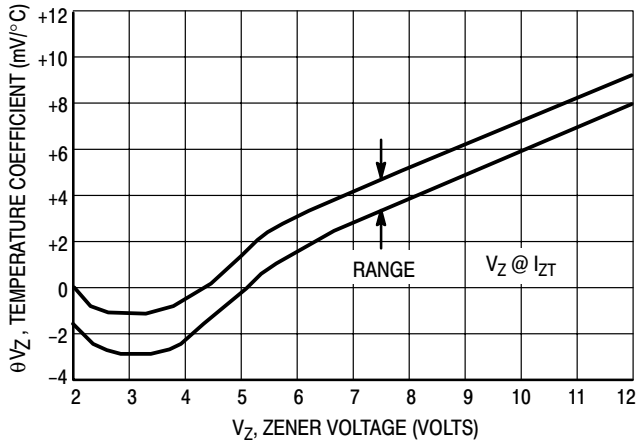


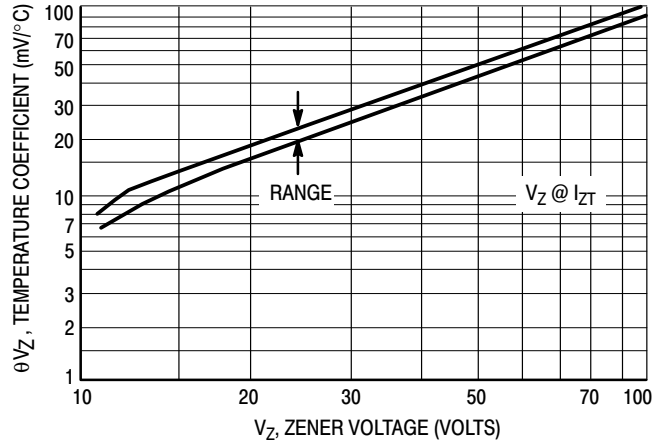
Figure 1. Power Temperature Derating Curve

# 1N4728A Series

a. Range for Units to 12 Volts

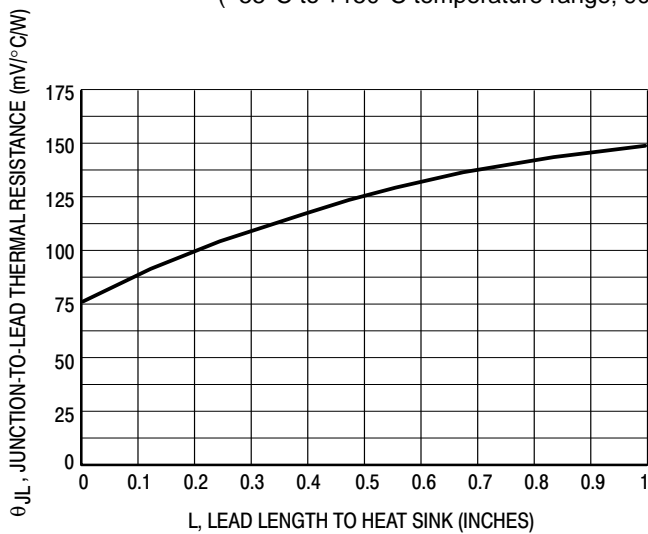


b. Range for Units to 12 to 100 Volts

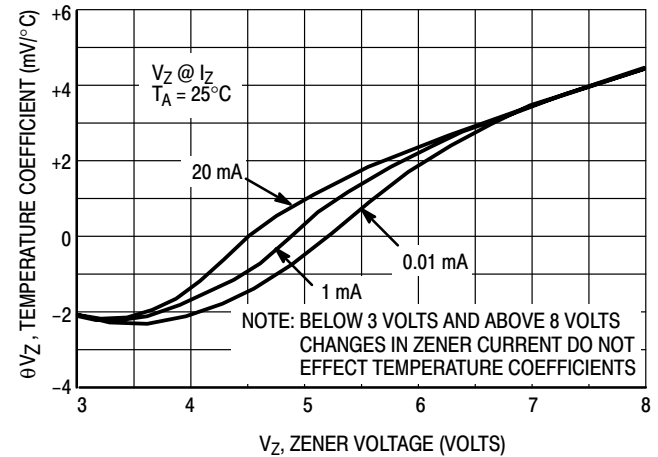


**Figure 2. Temperature Coefficients**

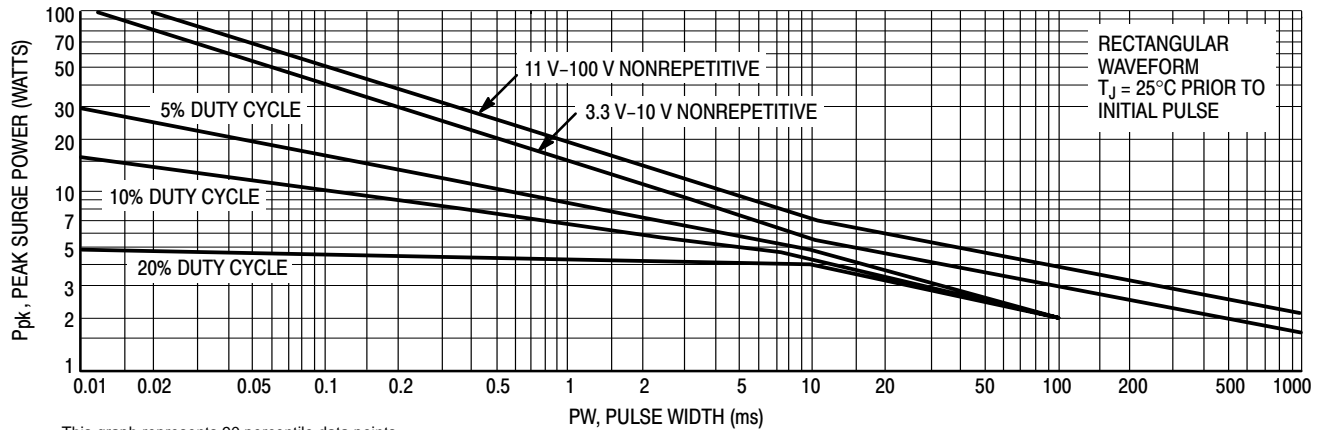
(-55°C to +150°C temperature range; 90% of the units are in the ranges indicated.)



**Figure 3. Typical Thermal Resistance versus Lead Length**



**Figure 4. Effect of Zener Current**



This graph represents 90 percentile data points.  
For worst case design characteristics, multiply surge power by 2/3.

**Figure 5. Maximum Surge Power**

# 1N4728A Series

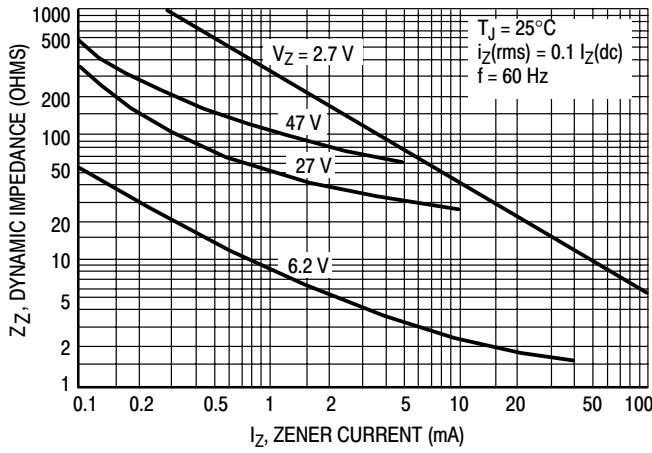


Figure 6. Effect of Zener Current on Zener Impedance

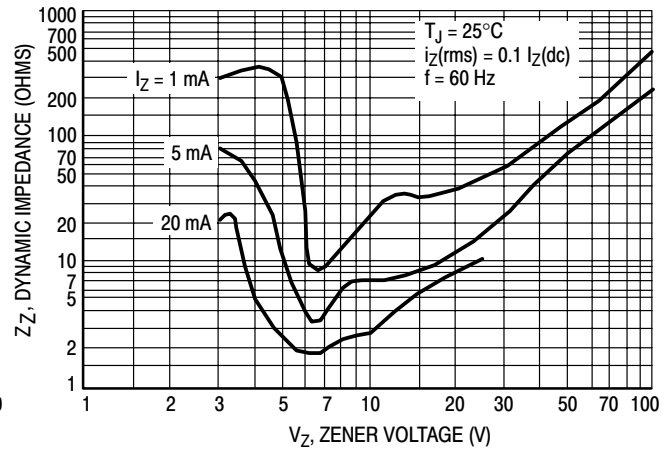


Figure 7. Effect of Zener Voltage on Zener Impedance

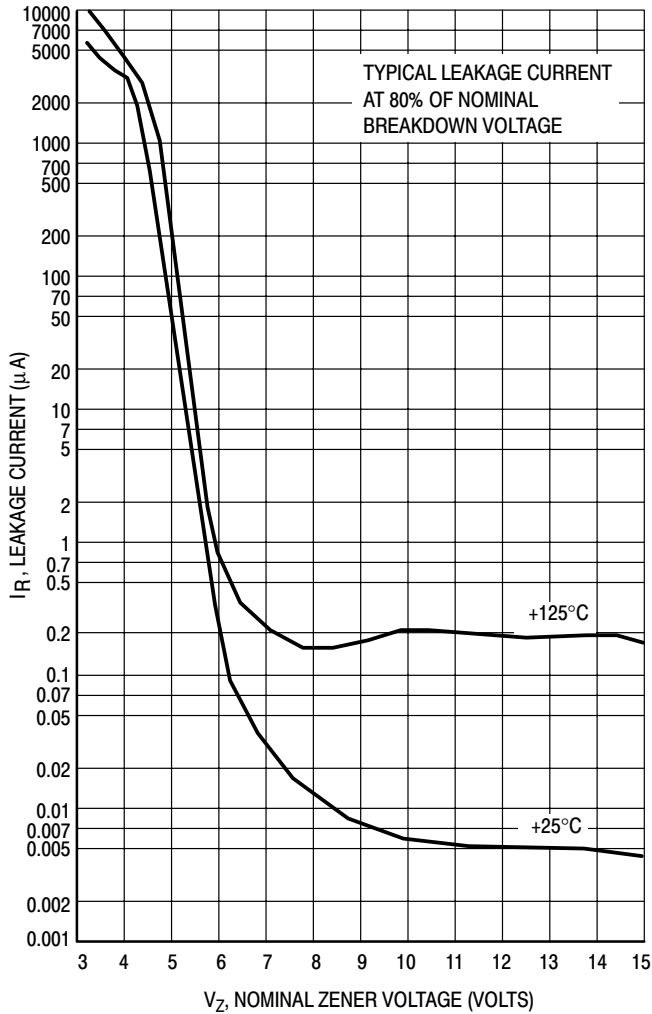


Figure 8. Typical Leakage Current

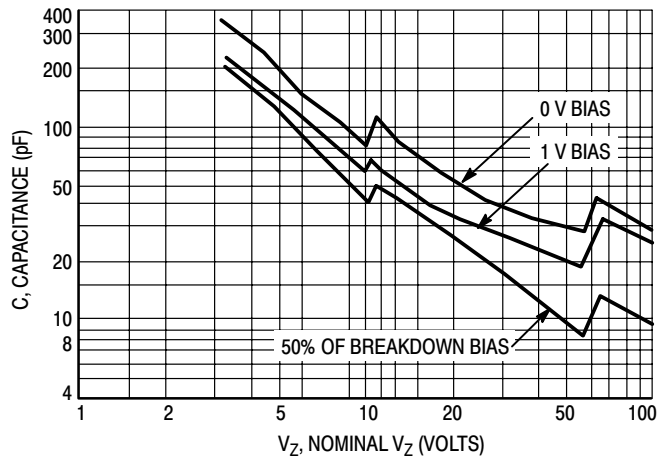


Figure 9. Typical Capacitance versus  $V_Z$

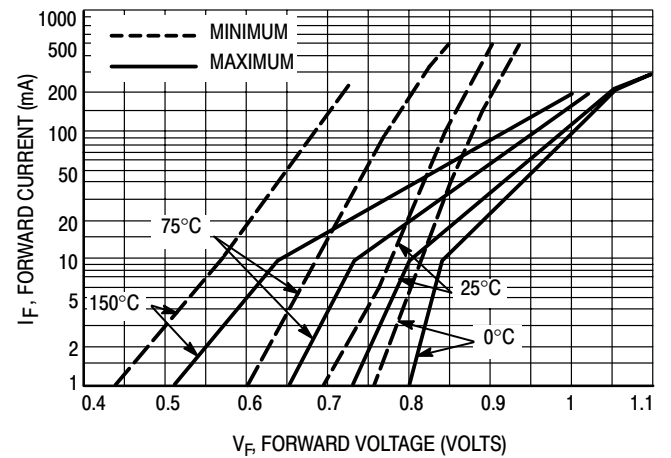


Figure 10. Typical Forward Characteristics

# 1N4728A Series

## APPLICATION NOTE

Since the actual voltage available from a given zener diode is temperature dependent, it is necessary to determine junction temperature under any set of operating conditions in order to calculate its value. The following procedure is recommended:

Lead Temperature,  $T_L$ , should be determined from:

$$T_L = \theta_{LA} P_D + T_A.$$

$\theta_{LA}$  is the lead-to-ambient thermal resistance ( $^{\circ}\text{C}/\text{W}$ ) and  $P_D$  is the power dissipation. The value for  $\theta_{LA}$  will vary and depends on the device mounting method.  $\theta_{LA}$  is generally 30 to  $40^{\circ}\text{C}/\text{W}$  for the various clips and tie points in common use and for printed circuit board wiring.

The temperature of the lead can also be measured using a thermocouple placed on the lead as close as possible to the tie point. The thermal mass connected to the tie point is normally large enough so that it will not significantly respond to heat surges generated in the diode as a result of pulsed operation once steady-state conditions are achieved. Using the measured value of  $T_L$ , the junction temperature may be determined by:

$$T_J = T_L + \Delta T_{JL}.$$

$\Delta T_{JL}$  is the increase in junction temperature above the lead temperature and may be found as follows:

$$\Delta T_{JL} = \theta_{JL} P_D.$$

$\theta_{JL}$  may be determined from Figure 3 for dc power conditions. For worst-case design, using expected limits of  $I_Z$ , limits of  $P_D$  and the extremes of  $T_J(\Delta T_J)$  may be estimated. Changes in voltage,  $V_Z$ , can then be found from:

$$\Delta V = \theta_{VZ} \Delta T_J.$$

$\theta_{VZ}$ , the zener voltage temperature coefficient, is found from Figure 2.

Under high power-pulse operation, the zener voltage will vary with time and may also be affected significantly by the zener resistance. For best regulation, keep current excursions as low as possible.

Surge limitations are given in Figure 5. They are lower than would be expected by considering only junction temperature, as current crowding effects cause temperatures to be extremely high in small spots, resulting in device degradation should the limits of Figure 5 be exceeded.